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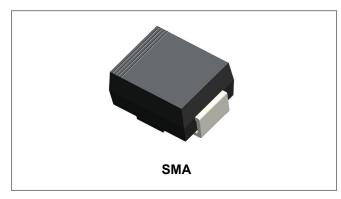








GS1A THRU GS1M 1.0A SURFACE MOUNT GLASS PASSIVATED RECTIFIER



Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop
- Low Power Loss
- Built-in Strain Relief
- Plastic Case Material has UL Flammability Classification Rating 94V-0
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: SMA molded plastic body
- Terminals: Solder plated, solderable per MIL-STD-750, Method 2026
- Polarity: Color band denotes cathode end
- Mounting Position: AnyWeight: 0.06 grams

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

| Characteristic | Symbol | GS1A | GS1B | GS1D | GS1G | GS1J | GS1K | GS1M | Units |
|-----------------------------------------------------------------------------------------------------------------------|--------------------------------------------------------|------|------|------|------------|------|------|------|-------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | V _{RRM} V _{RWM} V _R | 50 | 100 | 200 | 400 | 600 | 800 | 1000 | V |
| Maximum RMS voltage | V _{RMS} | 35 | 70 | 140 | 280 | 420 | 560 | 700 | V |
| Average Rectified Output Current @T _L = 100°C | lo | | , | | 1.0 | | | | Α |
| Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method) | I _{FSM} | | | | 30 | | | | Α |
| Forward Voltage @ I _F = 1.0 A | V _F | | | | 1.10 | | | | V |
| Peak Reverse Current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 125°C | I _{RM} | | | | 5.0 200 | | | | μA |
| Reverse Recovery Time(Note1) | t _{rr} | | | | 2.5 | | | | μS |
| Typical Junction Capacitance(Note2) | Сл | | | | 15 | | | | pF |
| Typical Thermal Resistance Junction to Lead (Note 3) | R _{0JL} | | | | 30 | | | | °C/W |
| Operating and Storage Temperature Range | T _J ,T _{STG} | | | -65 | to +175 | | | | °C |

Note: 1. Reverse recovery condition IF=0.5A, IR=1.0A, Irr=0.25A

- 2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
- 3. Mounted on P.C.B.with 8.0mm² land areas.
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Ratings and Characteristics Curves

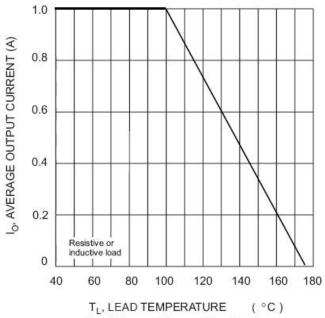
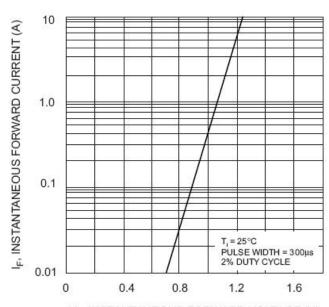


Fig. 1 Forward Current Derating Curve



V_F, INSTANTANEOUS FORWARD VOLTAGE (V) Fig. 2 Typical Forward Characteristics

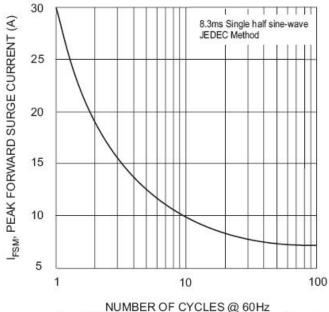
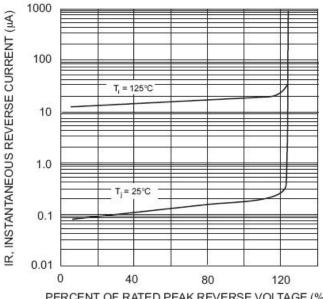


Fig. 3 Max Non-Repetitive Peak Fwd Surge Current



PERCENT OF RATED PEAK REVERSE VOLTAGE (%) Fig. 4 Typical Reverse Characteristics

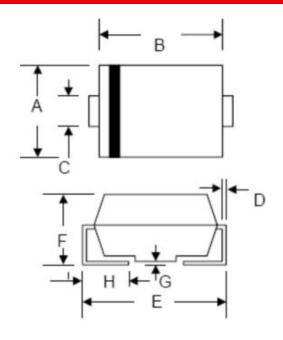
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Mechanical Dimensions SMA



| SYMBOL | Millir | meters | Inches | | |
|--------|--------|--------|--------|-------|--|
| STMBOL | Min. | Max. | Min. | Max. | |
| А | 2.40 | 2.84 | 0.094 | 0.112 | |
| В | 3.99 | 4.75 | 0.157 | 0.187 | |
| С | 1.05 | 1.70 | 0.041 | 0.067 | |
| D | 0.15 | 0.51 | 0.006 | 0.020 | |
| Е | 4.80 | 5.66 | 0.189 | 0.223 | |
| F | 1.90 | 2.95 | 0.075 | 0.116 | |
| G | 0.05 | 0.203 | 0.002 | 0.008 | |
| Н | 0.76 | 1.52 | 0.030 | 0.600 | |

Ordering Information

| Device | Package | Shipping |
|-----------|------------------|----------------|
| GS1A-GS1M | SMA (Pb-Free) | 5000pcs / reel |

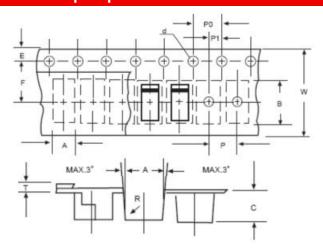
For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



First row: Part Number (GS1A, GS1B, GS1D, GS1G, GS1J, GS1K, GS1M) Second row: YYWWL YY is the manufacture year, WW is the manufacture week code, L is the wafer's Lot Number

Carrier Tape Specification SMA



| SYMBOL | Millimeters | | | |
|--------|-------------|-------|--|--|
| | Min. | Max. | | |
| Α | 2.97 | 3.17 | | |
| В | 5.70 | 5.90 | | |
| C | 2.32 | 2.52 | | |
| d | 1.40 | 1.60 | | |
| E | 1.40 | 1.60 | | |
| F | 5.60 | 5.70 | | |
| Р | 3.90 | 4.10 | | |
| P0 | 3.90 | 4.10 | | |
| P1 | 1.90 | 2.10 | | |
| T | 0.25 | 0.35 | | |
| W | 11.80 | 12.20 | | |

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